

Correlation lengths of Wigner crystal order in two dimensional electron system at high magnetic field

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The insulator terminating the fractional quantum Hall series at low Landau level filling ν is generally taken to be a pinned Wigner crystal (WC), and exhibits a microwave resonance that is interpreted as a WC pinning mode. Systematically studying the resonance in a high quality sample for carrier densities, n , between 1.8 and $5.7 \times 10^{10} \text{ cm}^{-2}$, we find maxima in resonance peak frequency, f_{pk} , vs magnetic field, B . L , the domain size, or correlation length of Wigner crystalline order, is calculated from f_{pk} . For each n , L vs ν tends at low ν toward a straight line with intercept; the linear fit is accurate over as much as a factor of 5 range of ν . We interpret the striking linear behavior as due to B compressing the electron wavefunctions, to alter the effective electron-impurity interaction.

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The nature of a two dimensional electron system (2DES) in high magnetic field (B) depends on the interactions of electrons with each other and with impurities, and on the overlap of individual electron wavefunctions. The size of an electron wavefunction, as measured by the magnetic length, $l_B = \sqrt{\hbar/eB}$, controls this overlap, and can also affect the electron-impurity interaction if the effective size or spacing of the impurities is comparable to l_B . In the high B limit, l_B vanishes, and electrons look like classical point particles. Without disorder, they are expected to form a Wigner crystal (WC), which is a triangular lattice stabilized by interelectron repulsion. Introduction of small amounts of disorder pins the WC, making it an insulator, and causing the crystalline order to have a finite correlation length or domain size. The wavefunction overlap increases as B is decreased from the high B limit; its importance is characterized by l_B/a , where a is the WC lattice constant, or equivalently by the Landau filling factor $\nu = nh/eB = (4\pi/\sqrt{3})(l_B/a)^2$. At sufficiently high ν , calculated [1, 2] for disorder free systems to be around 1/7, the WC ground state is predicted to undergo a transition to the fractional quantum Hall effect (FQHE)[3] liquids.

Experimentally, 2DES are insulators from the maximum B accessed down at least to the high B edge of the 1/5 FQHE plateau[4, 5]. Samples of sufficient quality to exhibit the 1/3 FQHE have a well-defined resonance[6, 7, 8, 9] in the microwave spectrum of the high B insulating phase. The natural interpretation of the resonance is as a pinning mode of the WC, in which regions of WC oscillate within the impurity potential that pins them. The average (per electron) restoring force constant, K , on static displacement away from equilibrium positions determines the frequency of the resonance peak. This force constant is $K = m^*\omega_0^2$, which defines ω_0 , the pinning frequency[10, 11], with m^* the carrier effective mass. In the magnetic field, cyclotron

motion mixes with the oscillation in the pinning potential for the resonating 2DES, resulting[10] in the observed resonance peak frequency $f_{pk} = \omega_0^2/2\pi\omega_c$, as long as the cyclotron frequency $\omega_c \ll \omega_0$, which must be the case for resonances in the frequency range of interest. In the classical, high B limit, in which l_B is much smaller than any feature of the disorder, and also small enough that wavefunction overlap of neighboring electrons can be neglected, ω_0 is constant in B , and $f_{pk} \propto 1/B$.

Correlation lengths of crystalline order, or domain sizes, can be calculated directly from f_{pk} and the elastic constants of the WC. Recent theories[12, 13, 14] identify the length directly relevant to f_{pk} as the Larkin length, L , over which displacements of equilibrium positions of electrons from perfect crystalline order reach the characteristic length of the electron-impurity interaction. In the classical, high B limit, the dependence of L on B has saturated, and L is a constant. Earlier theory[10, 11] considered the particular case of a sinusoidal charge density wave in magnetic field, and so obtained f_{pk} in terms of a correlation length that we denote L_a , over which displacements of equilibrium positions of electrons from perfect crystalline order reaches the lattice constant a .

This paper presents data on the microwave resonance for a high quality 2DES, surveyed over a wide range of B up to 20 T, and density, n between 5.7 and $1.8 \times 10^{10} \text{ cm}^{-2}$, to cover ν from 0.2 to 0.038. For all the n 's we looked at, the resonance peak frequency, f_{pk} , vs B exhibits a maximum. Most likely because of higher quality in the present sample, such a maximum was not found in previous studies[6, 7, 8, 9], in which f_{pk} vs B was increasing monotonically. We calculate L from f_{pk} and the theoretical shear modulus of a WC of classical point particles, and find L in the range of 0.23 to 0.71 μm . Plots of L vs ν (with n fixed) tend toward a straight line with intercept, L_∞ , at low ν , with upward curvature developing at most n 's as $\nu = 1/5$ is approached from below. The

linear form for the L vs ν data is quantitatively convincing for the lowest few densities surveyed; at the lowest n there is a precise fit to the data over a factor of 5 in ν . The large ranges of linear fit for low n , extending to such low ν , suggest the linear behavior is an effect of the interplay of l_B and impurity correlation lengths. We interpret the upward curvature that sets in at higher ν as an effect of the correlations responsible for the FQHE.

The microwave measurement methods used here are similar to those described in earlier publications [8, 9]. The inset to Fig. 1 shows a sketch of the sample. Metal film, shown as black in the figure, was patterned onto the top of the sample to form a coplanar transmission line consisting of a 45 μm wide center strip separated from side planes by slots of width $W = 30 \mu\text{m}$. The narrow center conductor was driven and the two side conductors were grounded, and the line coupled capacitively to the 2DES. The geometry confines the microwave field mainly to the regions of 2DES under the slots.

The transmitted microwave power was measured and normalized to unity for the case of vanishing σ_{xx} , obtained by depleting the 2DES with backgate voltage. The experiment is sensitive to σ_{xx} with wavevector $q \lesssim 2\pi/W$; we regard the 2DES as in the $q = 0$ limit in calculating the real part of diagonal conductivity, $\text{Re}(\sigma_{xx})$, from the microwave absorption. We used $\text{Re}(\sigma_{xx}) = W |\ln P| / 2Z_0 d$, where P is the normalized transmitted power, $Z_0 = 50\Omega$, the $\sigma_{xx} = 0$ characteristic impedance, and $d = 28 \text{ mm}$ is the total length of the transmission line. This formula is valid in the high f , low loss limit, in the absence of reflections. Detailed simulation of the transmission line with 2DES in the quasi-TEM approximation indicates this formula is correct to about 15% under experimental conditions. The apparatus is typically 20 times more sensitive to $\text{Re}(\sigma_{xx})$ than it is to $\text{Im}(\sigma_{xx})$. The temperature of all measurements presented here was $\sim 50 \text{ mK}$. Microwave power was varied to ensure that the measurement was in a linear regime at the operating temperature.

The data were taken on a AlGaAs/GaAs heterojunction sample with as-cooled density (n) of $6.0 \times 10^{10} \text{ cm}^{-2}$ and 0.3 K mobility of $6 \times 10^6 \text{ cm}^2/\text{V s}$. The sample was not illuminated, and its density was varied down to $1.8 \times 10^{10} \text{ cm}^{-2}$ by application of a voltage between a backgate and an ohmic contact, placed outside the transmission line film.

Figure 1 shows traces of $\text{Re}(\sigma_{xx})$ vs B in the quantum Hall regime for three different n 's, for $f = 0.4$ or 0.5 GHz. The 1/3 FQHE is present for all n we survey; even the lowest n , $1.8 \times 10^{10} \text{ cm}^{-2}$, in Figure 1a, exhibits well defined FQH features, indicating the 2DES remains reasonably homogenous even at the large backgate bias required to produce that n . The 1/5 FQHE, however, is only present for larger n , as seen in Figure 1b, where a 1/5 FQHE minimum in $\text{Re}(\sigma_{xx})$ vs B is present for $n \approx 5.3 \times 10^{10} \text{ cm}^{-2}$ but absent for $4.0 \times 10^{10} \text{ cm}^{-2}$.

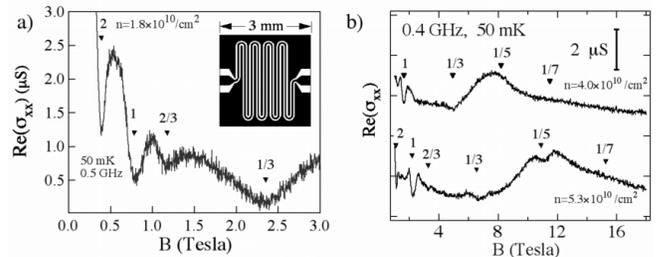


FIG. 1: Real part of diagonal conductivity $\text{Re}(\sigma_{xx})$ vs magnetic field, B , for the sample at three different carrier densities n , filling factors ν marked as inverted triangles. *a.* $n = 1.8 \times 10^{10} \text{ cm}^{-2}$. Inset shows top view of transmission line, where black indicates metal film. *b.* $n = 4.0 \times 10^{10} \text{ cm}^{-2}$ and $n = 5.3 \times 10^{10} \text{ cm}^{-2}$.

The traces of Figure 1b show broad peaks beginning just above the 1/3 FQHE. These peaks are the manifestations in $\text{Re}(\sigma_{xx})$ of the rapidly rising dc ρ_{xx} vs B [5, 15], observed on increasing B beyond the 1/3 FQHE. The 1/5 FQHE minimum for $n \approx 4.0 \times 10^{10} \text{ cm}^{-2}$ is superimposed on that peak.

Figure 2 shows typical resonance spectra, $\text{Re}(\sigma_{xx})$ vs f , taken at various n and B . Spectra for several B are shown in Figure 2a for $n = 1.8 \times 10^{10} \text{ cm}^{-2}$ and in Figure 2b for $n = 5.3 \times 10^{10} \text{ cm}^{-2}$. For ν just below 1/5, the resonance is present but comparatively broad; increasing B initially sharpens the peak and shifts it to higher f . At some n -dependent magnetic field, the resonance peak frequency, f_{pk} , goes through a maximum and begins to shift *downward* as B is increased further. The reduction of f_{pk} continues, and the resonance remains well-developed, out to the maximum B measured. The maximum f_{pk} occurs around 10 T ($\nu = 0.074$) for the $n = 1.8 \times 10^{10} \text{ cm}^{-2}$ and around 15 T ($\nu = 0.146$) for $n = 5.3 \times 10^{10} \text{ cm}^{-2}$.

Figure 2c shows resonance spectra for fixed $B = 18 \text{ T}$ as n is varied. The resonances shift to higher f and broaden as n is decreased. Upward shift and broadening as n is decreased at fixed B is seen for all B where the resonance is observed, and has been observed in other samples [6, 9] as well.

Figure 3a shows f_{pk} vs ν for the various n 's we studied. Each curve exhibits a maximum in f_{pk} , and the maxima shift generally to lower ν as n decreases. Full width at half maximum linewidths, Δf , are plotted against the same axis in Figure 3b. These increase rapidly as the transition to the FQH liquid is approached. Around the ν where f_{pk} is maximal, the corresponding Δf curve for the same n shows a local minimum.

The increasing f_{pk} vs ν curves (for fixed n) on the low ν side of the maxima may be viewed only as the approach to the classical regime in which $f_{pk} \propto \nu$ is expected. The observed increase is sublinear, and while the increase of f_{pk} with ν is a hint toward the classical behavior, the fully classical, point particle picture is not applicable. The decreasing f_{pk} vs ν (increasing f_{pk}

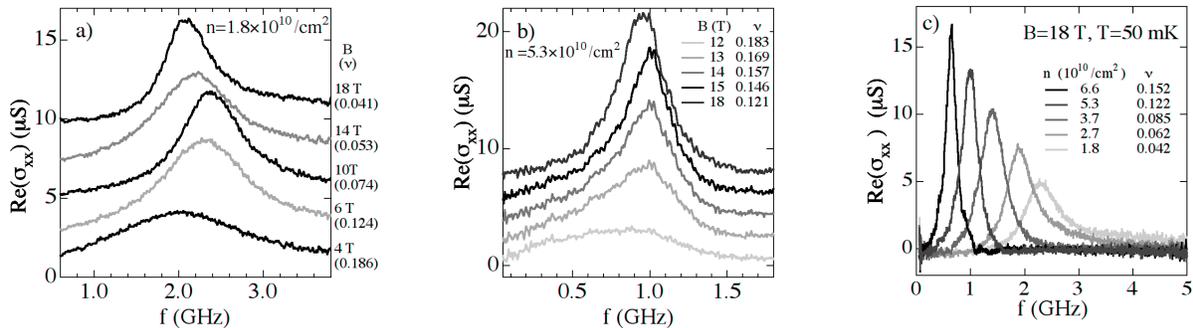


FIG. 2: Resonance spectra, real part of diagonal conductivity, $\text{Re}(\sigma_{xx})$, vs frequency f . *a.* Density $n = 1.8 \times 10^{10} \text{ cm}^{-2}$, various magnetic fields B . Successive curves offset in steps of $2.5 \mu\text{S}$, for clarity; the 4 T curve is not offset. *b.* Density $n = 5.3 \times 10^{10} \text{ cm}^{-2}$, various B . Successive curves offset in steps of $2.0 \mu\text{S}$, for clarity. *c.* Various n , for fixed $B = 18 \text{ T}$, $T = 50 \text{ mK}$.

vs B), seen in the present data set on the high ν side of the maxima, and throughout previous data sets[7, 8], has been interpreted in theories[12, 13, 14] based on an interplay of l_B and some disorder correlation length, ξ , whose definition depends on the model of disorder. The calculations, taken for weak disorder with small $\xi \ll l_B$, give[12] $f_{pk} \propto B$, or[13, 14] $f_{pk} \propto B^2$.

To more simply interpret the behavior of f_{pk} vs ν we recast the f_{pk} data into domain size, L , using the elastic coefficients of the classical WC. L is the localization length of transverse phonons in the $B = 0$ crystal[14, 16]. The angular pinning frequency, $\omega_0 = c_t 2\pi/L$, where c_t is the $B = 0$ transverse phonon propagation velocity, $c_t = (\mu_t/nm^*)^{1/2}$. μ_t is the shear modulus. A WC of classical point particles[17] has shear modulus $\mu_{t,cl} = 0.245e^2n^{3/2}/4\pi\epsilon_0\epsilon$, where we take $\epsilon = 12.8$ the GaAs host dielectric constant. ω_0 is gotten from f_{pk} data using the well-known formula[10] for $\omega_0 \ll \omega_c$ to take care of the effect of the Lorentz force on the dynamics, $\omega_0 = (2\pi f_{pk}\omega_c)^{1/2}$. With the classical shear modulus $\mu_{t,cl}$ we then get $L = (2\pi\mu_{t,cl}/neBf_{pk})^{1/2}$.

Figure 4 shows plots of the calculated L vs ν for all the n 's we measured. Panels a and b of the figure show the same data, with successive curves offset for clarity only in panel a. Most striking are the data for the smallest n , $1.8 \times 10^{10} \text{ cm}^{-2}$, which fit a straight line over the *entire range* of measurement of the resonance, over a factor of 5 in ν . The fit is accurate to within the instrumental errors in L , which we estimate as about $\pm 0.02 \mu\text{m}$, propagating mainly from error in f_{pk} . The plots for all the other n tend to curve upwards for larger ν , as $1/5$ is approached. For the lower n 's, the linear behavior holds over substantial ranges of ν and is quantitatively demonstrated.

The straight line regions of the L vs ν plots extend out to extremely low ν , so it is natural to interpret the linear behavior as an effect of electron-disorder interaction rather than interelectron wavefunction overlap. Particularly if it is due to interface roughness[12], the disorder potential can vary on extremely small length scales,

down to about the lattice constant of GaAs. The small lengthscales associated with the disorder would make the effects of electron-disorder interaction saturate less easily at high B than interelectron wavefunction overlap effects.

Because of the clear linear behavior for the lowest few n 's, we fit the low ν tails of all the L vs ν plots to $L = \beta\nu + L_\infty$, where β and L_∞ are the fit parameters, and L_∞ is the domain size extrapolated to infinite B . The least squares fits are shown as heavy lines in Figure 4a, and extend over the points that were included in the fits. The inset to Figure 4b shows the parameters of the least squares fits. The curves appear irregular for larger n , and are more reliable for small n , where the linear ranges of L vs ν are substantial. For $n = 1.8 \times 10^{10} \text{ cm}^{-2}$, $L_\infty \approx 0.17 \mu\text{m} \approx 2.1a$. [18]

In the weak pinning energy limit, random pinning models[12]-[14] predict $L \sim n$, so that L increases when the WC is stiffer. $L \sim n$ may explain why the low n , low ν data of Figure 4b group so closely when plotted against the Landau filling, which contains the density as well as the magnetic length, $\nu = 2\pi n l_B^2$. L_∞ vs n may give some insight into the nature of the pinning in the limit where electrons look like point particles. In the inset to Figure 4b, L_∞ vs n clearly increases, as expected for weak pinning. For $n \leq 4.2 \times 10^{10} \text{ cm}^{-2}$, L_∞ vs n in the inset to that figure is roughly linear, with a fit resulting in a slope of $2.3 \times 10^{-22} \text{ m}^3$, and intercept of $0.13 \mu\text{m}$.

We interpret the upward curvature of the L vs ν data as $1/5$ is approached (except for $n = 1.8 \times 10^{10} \text{ cm}^{-2}$) as effects of correlations related to the FQHE, which require interelectron overlap. One possibility is that μ_t is decreasing as $1/5$ is approached due to these correlations, as predicted in a recent theory[19] of a WC made up of composite fermions. L presented in Figure 4 is calculated using the classical shear modulus, $L \sim \mu_{t,cl}^{1/2}$, and would *overestimate* the true domain size, \tilde{L} , if the true shear modulus μ_t is less than $\mu_{t,cl}$. This overestimation in the L data would result in upward curvature of the plots,

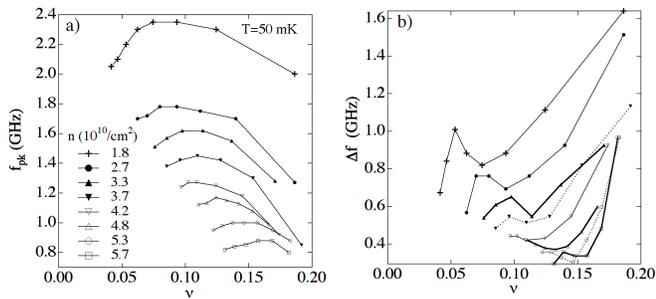


FIG. 3: *a.* Peak frequency f_{pk} vs Landau filling ν for different carrier densities, n . *b.* Full width at half maximum linewidth, Δf , vs ν . Symbols are same as in panel *a*.

even if the underlying \tilde{L} vs ν were straight lines, like the $n = 1.8 \times 10^{10} \text{ cm}^{-2}$ plot in Figure 4. We interpret the reduction in the curvature at low n as due to the suppression of the FQH type correlations, owing to the increased importance of disorder relative to electron-electron interaction at lower n . This is consistent with Figure 1b, in which the $1/5$ feature is suppressed at lower n .

In summary, systematic studies of the microwave resonance for many n 's show maxima in f_{pk} vs ν ; these curves are greatly simplified on converting f_{pk} into a domain size L . L vs ν fits a straight line for low n and low ν , but curves upward as $\nu = 1/5$ is approached. The straight line behavior is interpreted as an effect of interplay between electron wavefunctions and disorder features; the upward curvature is interpreted as an effect of FQH-type correlations, possibly associated with softening of the WC.

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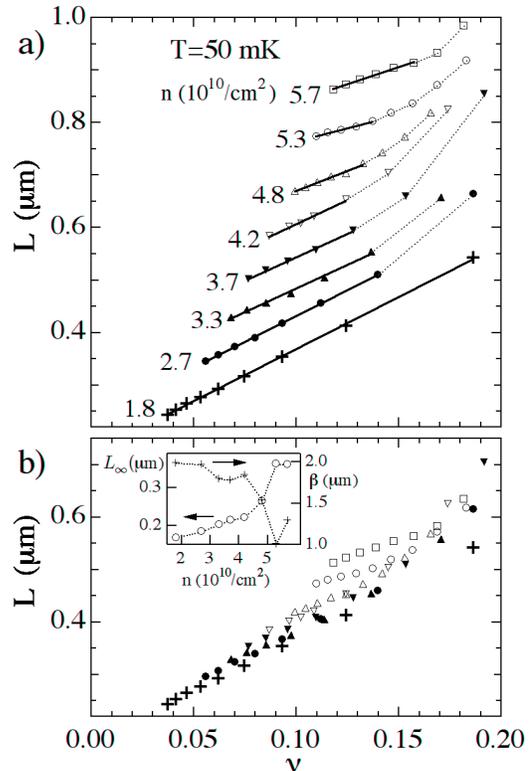


FIG. 4: Calculated domain sizes L , vs Landau filling ν for various carrier densities n . *a.* Successive curves are offset from each other by $0.05 \mu\text{m}$. Curves are labeled with n (10^{10} cm^{-2}). Heavy lines are linear least squares fits to $L = \beta\nu + L_\infty$, extending over ranges of ν that were fit. *b.* Same data as in panel *a*, but not offset. Symbols for the various n are the same as in *a*. Inset shows fit parameters, β and L_∞ , vs n .

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